

Thermally-Enhanced High Power RF GaN HEMT

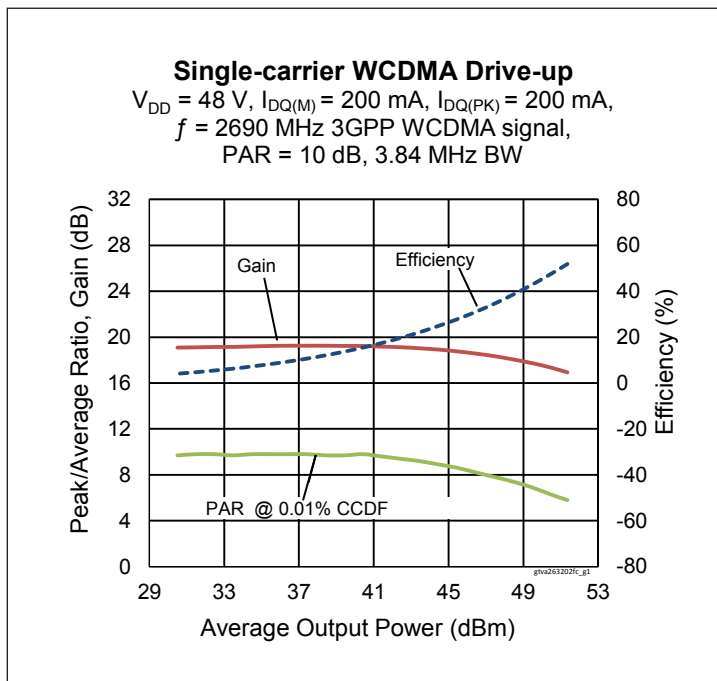
340 W, 48 V, 2620 – 2690 MHz

Description

The GTVA263202FC is a 340-watt (P_{3dB}) GaN high electron mobility transistor (HEMT) for use in multi-standard cellular power amplifier applications. It features input matching, high efficiency, and a thermally-enhanced surface-mount package with earless flange.



GTVA263202FC
Package H-37248-4



Features

- GaN HEMT technology
- Input matched
- Typical pulsed CW performance, 2690 MHz, 48 V, combined outputs
 - Output power at $P_{3dB} = 340\text{ W}$
 - Drain efficiency = 70%
 - Gain = 16 dB
- Capable of handling 10:1 VSWR @ 48 V, 80 W (CW) output power
- Human Body Model Class 1B (per ANSI/ESDA/ JEDEC JS-001)
- Low thermal resistance
- Pb-free and RoHS compliant

RF Characteristics

Single-carrier WCDMA Specifications (tested in Infineon production test fixture)

$V_{DD} = 48\text{ V}$, $I_{DQ} = 200\text{ mA}$ (per side), $P_{OUT} = 80\text{ W}$ avg, $f = 2690\text{ MHz}$, 3GPP signal, channel bandwidth = 3.84 MHz, peak/average = 10 dB @ 0.01% CCDF

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	G_{ps}	16	17	—	dB
Drain Efficiency	η_D	34	40	—	%
Adjacent Channel Power Ratio	ACPR	—	-29	-26.5	dBc

All published data at $T_{CASE} = 25^\circ\text{C}$ unless otherwise indicated

ESD: Electrostatic discharge sensitive device—observe handling precautions!

DC Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-source Breakdown Voltage	$V_{GS} = -8\text{ V}$, $I_D = 21\text{ mA}$	$V_{(BR)DSS}$	150	—	—	V
Drain-source Leakage Current	$V_{GS} = -8\text{ V}$, $V_{DS} = 10\text{ V}$	I_{DSS}	—	—	5	mA
Gate Threshold Voltage	$V_{DS} = 10\text{ V}$, $I_D = 21\text{ mA}$	$V_{GS(th)}$	-3.8	-3.0	-2.3	V

Recommended Operating Conditions

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Drain Operating Voltage		V_{DD}	0	—	50	V
Gate Quiescent Voltage	$V_{DS} = 50\text{ V}$, $I_D = 200\text{ mA}$	$V_{GS(Q)}$	—	-2.8	—	V

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source Voltage	V_{DSS}	125	V
Gate-source Voltage	V_{GS}	-10 to +2	V
Gate Current	I_G	20	mA
Drain Current	I_D	7.5	A
Junction Temperature	T_J	225	°C
Storage Temperature Range	T_{STG}	-65 to +150	°C

Operation above the maximum values listed here may cause permanent damage. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the component. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. For reliable continuous operation, the device should be operated within the operating voltage range (V_{DD}) specified above.

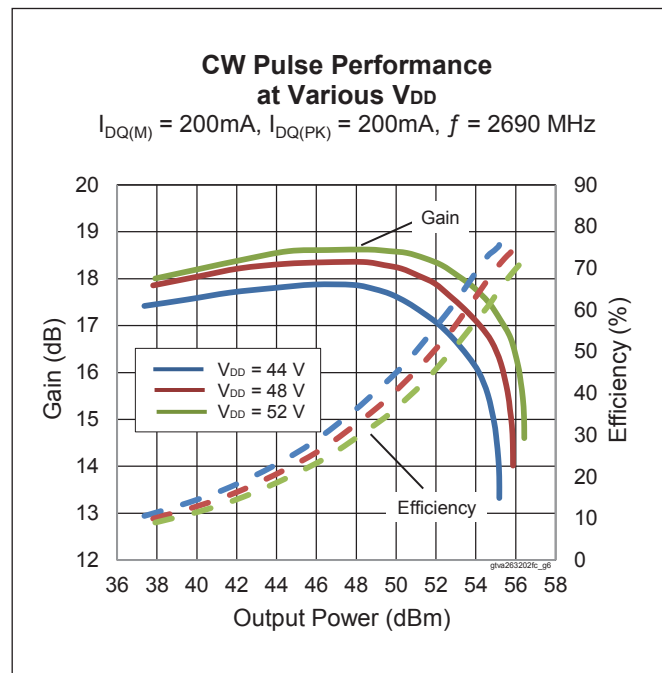
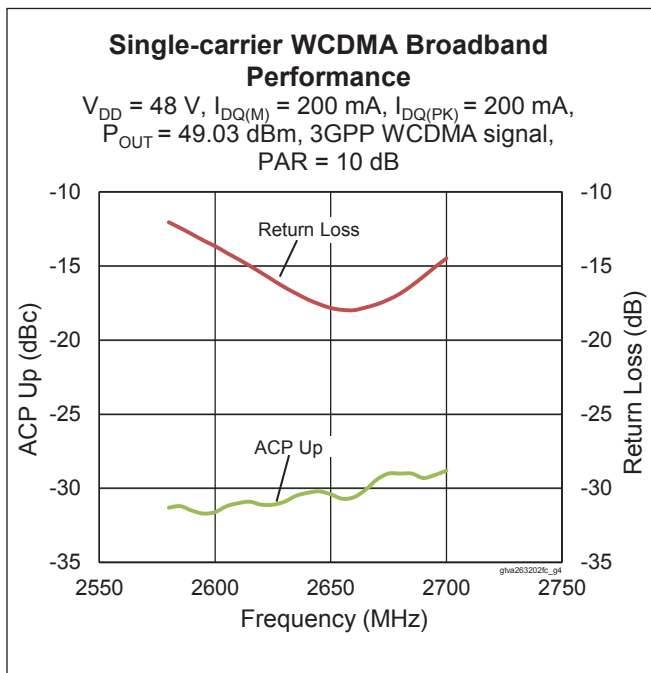
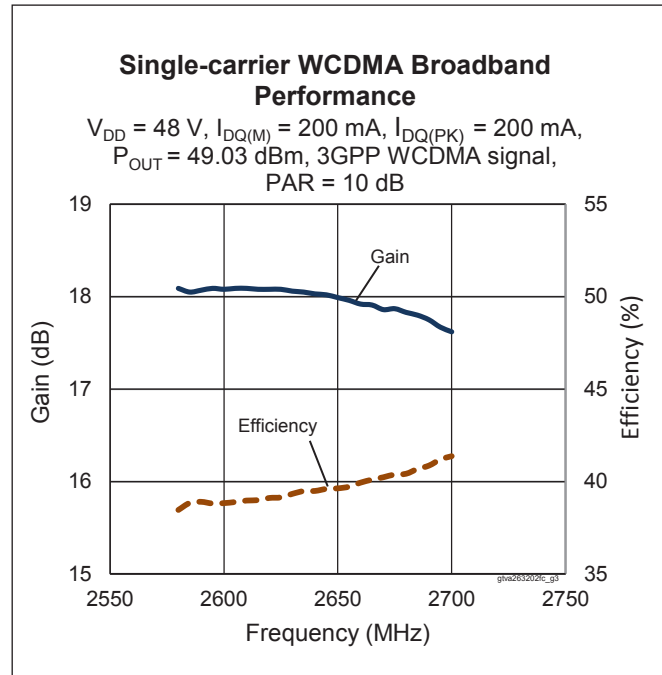
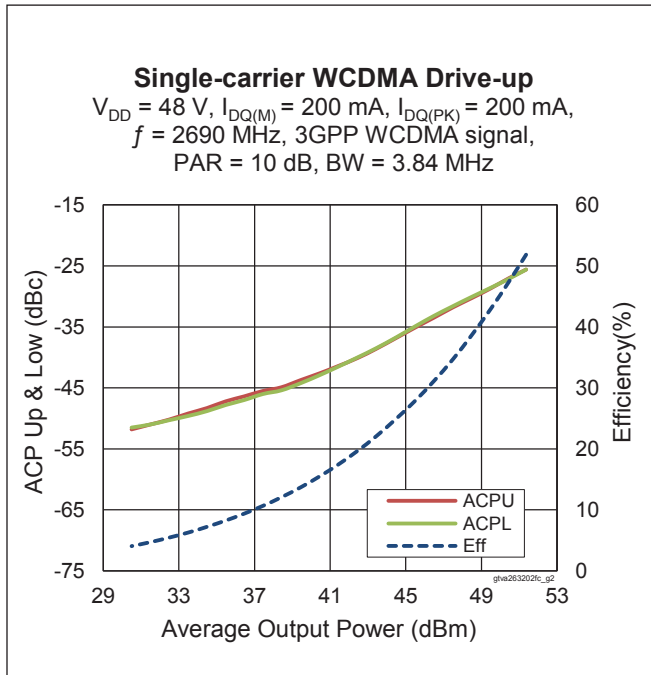
Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance ($T_{CASE} = 70\text{ °C}$, 80 W (CW))	$R_{\theta JC}$	0.5	°C/W

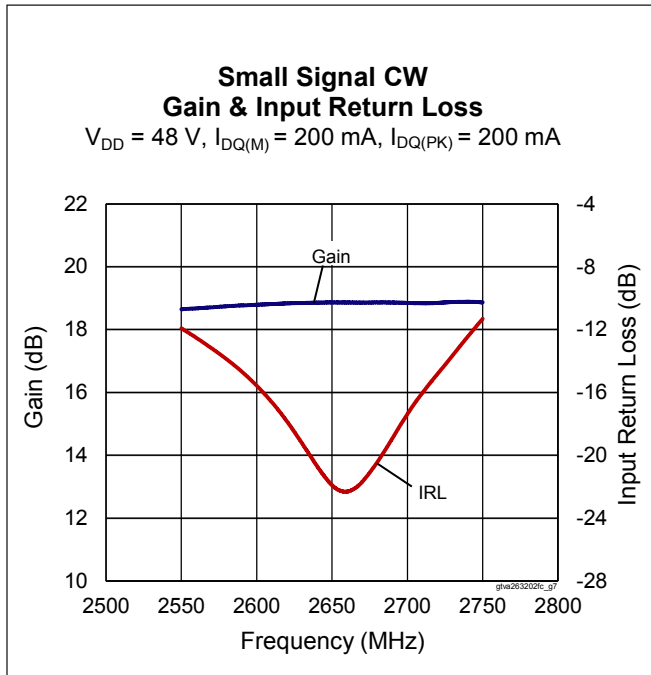
Ordering Information

Type and Version	Order Code	Package Description	Shipping
GTVA263202FC V1 R0	GTVA263202FCV1R0XTMA1	H-37248-4, earless flange	Tape & Reel, 50 pcs
GTVA263202FC V1 R2	GTVA263202FCV1R2XTMA1	H-37248-4, earless flange	Tape & Reel, 250 pcs

Typical Performance (data taken in a production test fixture)



Typical Performance (cont.)

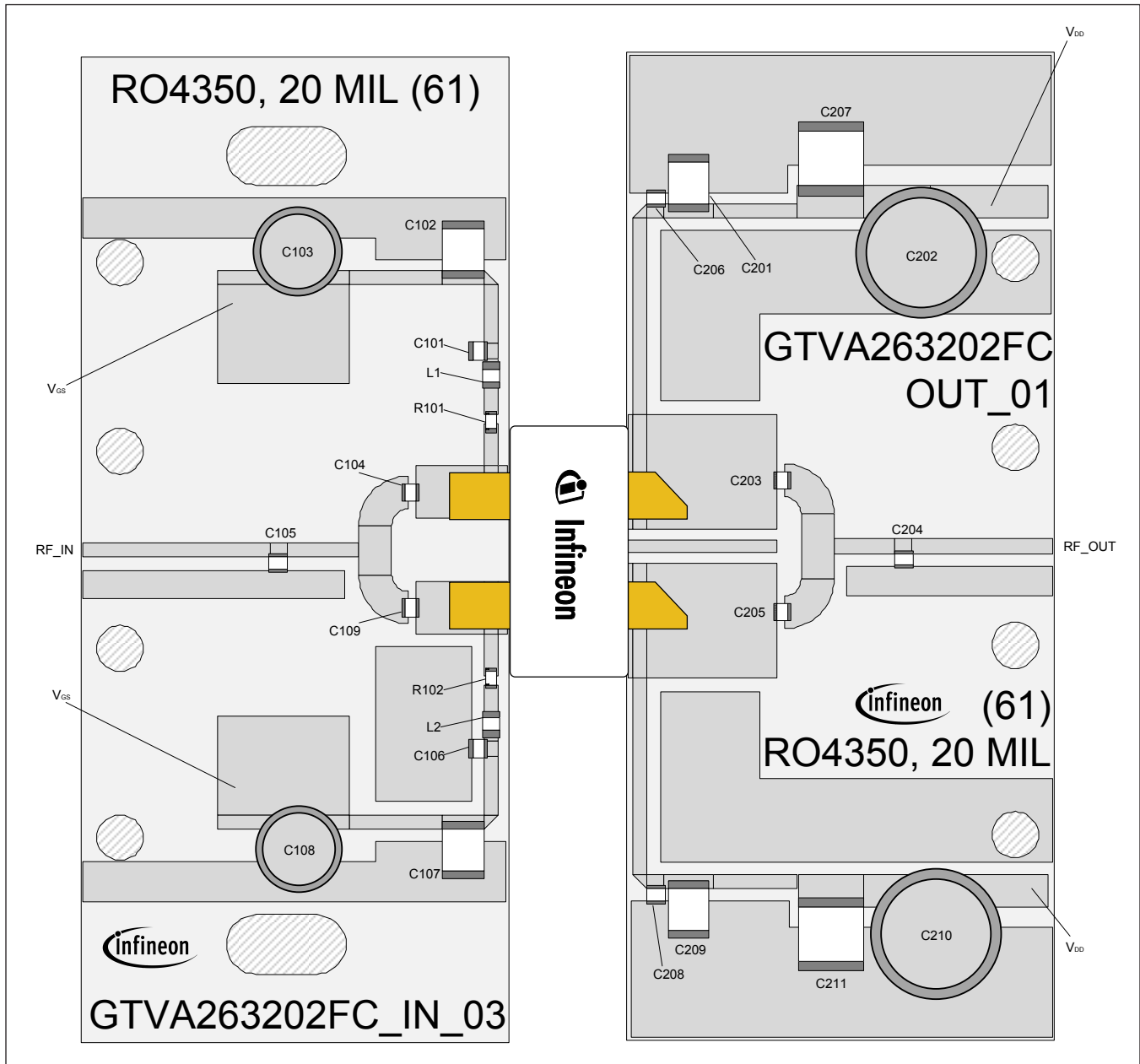


Load Pull Performance

Load Pull Performance (per side) – Pulsed CW signal: 10 μs , 10% duty cycle, 48 V, $I_{DQ} = 200\text{ mA}$

Freq [MHz]	Z_s [Ω]	P_{3dB}									
		Max Output Power					Max PAE				
		Z_L [Ω]	Gain [dB]	P_{OUT} [dBm]	P_{OUT} [W]	PAE [%]	Z_L [Ω]	Gain [dB]	P_{OUT} [dBm]	P_{OUT} [W]	PAE [%]
2620	8.5 – j7	2.45 – j3.5	14.95	53.75	237	65.9	2.0 – j1.1	16.36	51.13	130	77.3
2655	8.9 – j8.5	2.96 – j3.6	14.67	53.77	238	67.7	2.43 – j1.8	15.88	52.39	173	77.2
2690	9.7 – j9.7	3.0 – j3.86	14.5	53.75	237	68.2	2.17 – j1.9	15.84	52.02	159	77.6

Reference Circuit, 2620 - 2690 MHz



Reference circuit assembly diagram (not to scale)

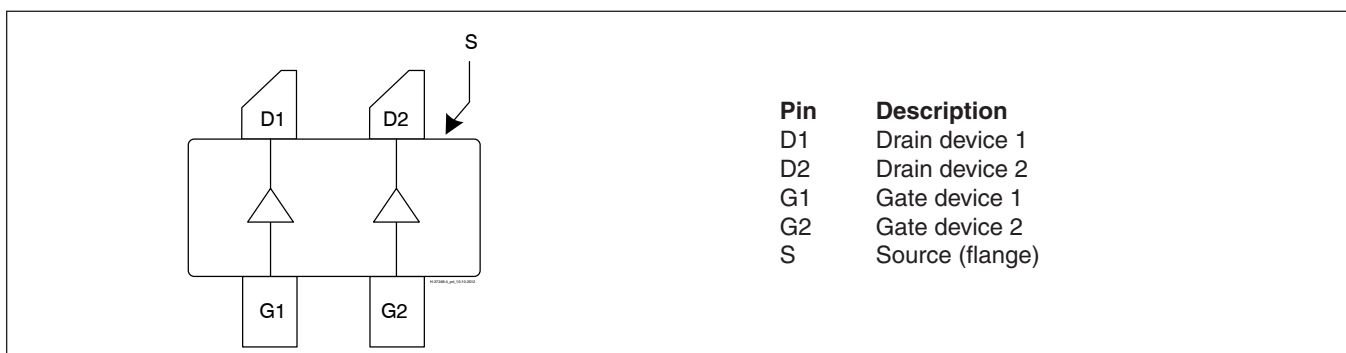
Reference Circuit (cont.)

Reference Circuit Assembly

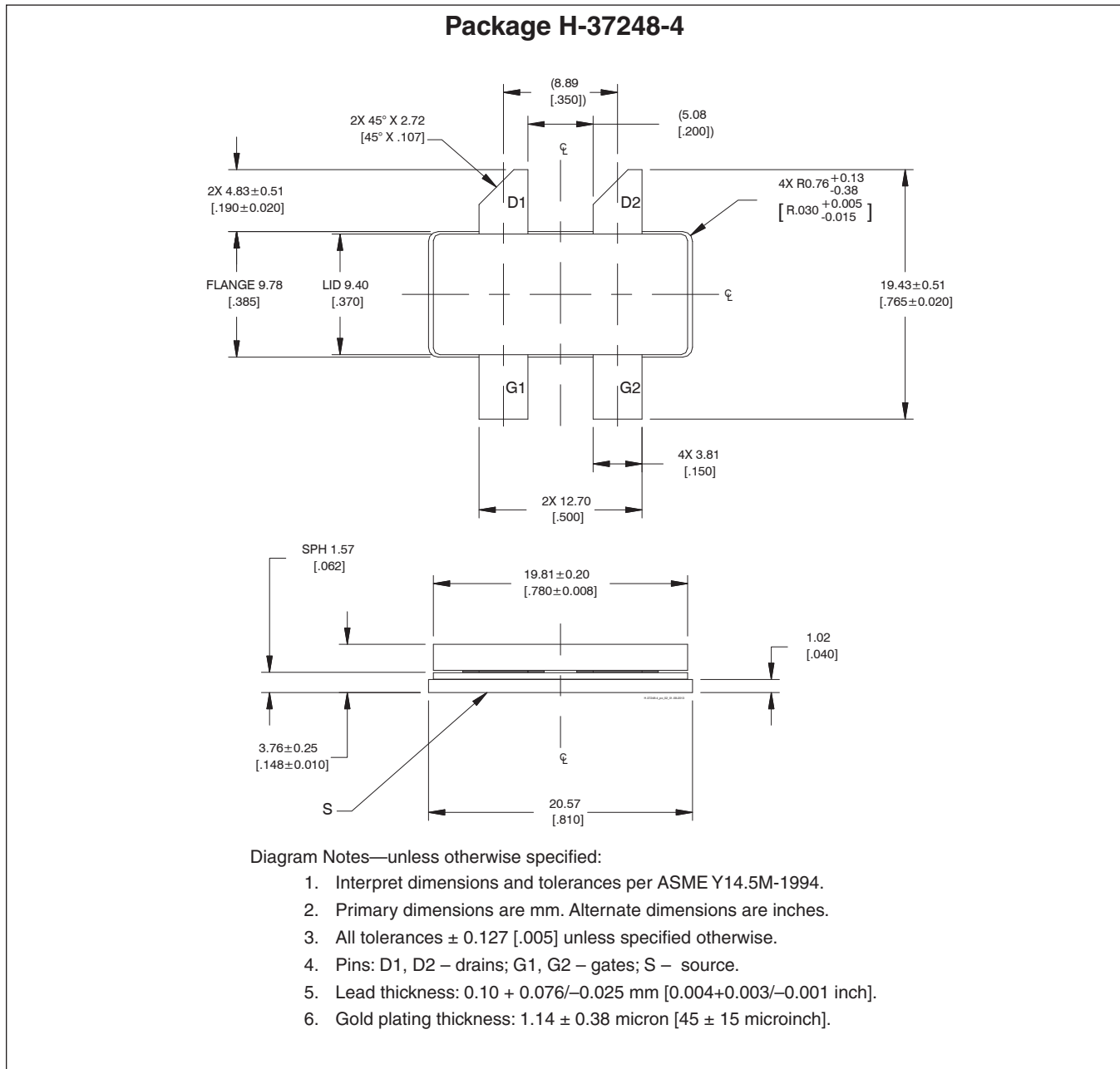
DUT	GTVA263202FC V1
Test Fixture Part No.	LTN/GTVA263202FC V1
PCB	Rogers 4350, 0.508 mm [0.020"] thick, 2 oz. copper, $\epsilon_r = 3.66$, $f = 2620 - 2690$ MHz
Find Gerber files for this test fixture on the Infineon Web site at http://www.infineon.com/rfpower	

Components Information

Component	Description	Manufacturer	P/N
Input			
C101, C104, C106, C109	Capacitor, 10 pF	ATC	ATC800A100JT250T
C102, C107	Capacitor, 1 μ F	TDK Corporation	C4532X7R2A105M230KA
C103, C108	Capacitor, 10 μ F	Panasonic Electronic Components	EEE-HB1H100AP
C105	Capacitor, 1 pF	ATC	ATC800A1R0CT250T
L1, L2	Inductor, 12 nH	Coilcraft	0908SQ-12NGLB
R101, R102	Resistor, 5.6 ohms	Panasonic Electronic Components	ERJ-3GEYJ5R6V
Output			
C201, C209	Capacitor, 1 μ F	TDK Corporation	C4532X7R2A105M230KA
C202, C210	Capacitor, 220 μ F	Panasonic Electronic Components	ECA-2AHG221
C203, C205, C206, C208	Capacitor, 10 pF	ATC	ATC800A100JT250T
C204	Capacitor, 1.4 pF	ATC	ATC800A1R4CT250T
C207, C211	Capacitor, 10 μ F	TDK Corporation	C5750X7S2A106M230KB

Pinout Diagram (top view)


Package Outline Specifications



Find the latest and most complete information about products and packaging at the Infineon Internet page <http://www.infineon.com/rfpower>

Revision History

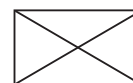
Revision	Date	Data Sheet	Page	Subjects (major changes since last revision)
01	2016-01-14	Advance	All	Data Sheet reflects advance specification for product development
02	2016-08-30	Production	All	Data Sheet reflects released product specification
03	2017-04-06	Production	1 2	Remove "Integrated ESD protection" from Features Restructure tables for clarity.

We Listen to Your Comments

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